NSN 5961-01-150-8678

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-150-8678 **Inclosure Material:** Metal **Overall Length:** 0.380 inches **Overall Height:** 1.170 inches **Overall Width:** 0.175 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 repetitive peak off-state voltage and 30.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 100.00 amperes forward current, total rms megawatts and 3.00 amperes forward current, total rms of standard range **Power Rating Per Characteristic:** 20.0 watts small-signal input power, common-collector not applicable and 0.5 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpnp **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: